

2MBI300VJ-120-50

IGBT Modules

IGBT MODULE (V series) 1200V / 300A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

■ Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions	Conditions		Units	
Collector-Emi	Collector-Emitter voltage					V	
Gate-Emitter v	oltage	V _{GES}			±20	V	
0			Continuous	Tc=25°C	450		
ırte	Collector current	Ic	Continuous	Tc=100°C	300		
S Collector curr		lc pulse	1ms		600	Α	
드		-lc			300		
			1ms		600		
Collector power dissipation		Pc	1 device		1595	W	
Junction temperature		Tj			175		
Operating junction temperature (under switching conditions)		T _{jop}			150	°C	
Case temperature		Tc			125		
Storage temperature		Tstg			-40 to +125		
Isolation voltage	lation voltage between terminal and copper base (*1)		AC : 1min.		2500	VAC	
	between thermistor and others (*2)	Viso	AO : IIIIII.		2300	VAO	
	Mounting (*3)				3.5		
Screw torque	Terminals (*4)	-			4.5	N m	
	PC-Board (*5)				0.6		

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test. Note *3: Recommendable value : 2.5-3.5 Nm (M5) Note *4: Recommendable value : 3.5-4.5 Nm (M6) Note *5: Recommendable value : 0.4-0.6 Nm (M2.5)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Symbolo	Conditions	anditions		Characteristics			
ite	ems	Symbols	Conditions		min.	typ.	max.	Units	
	Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	3.0	mA	
	Gate-Emitter leakage current	Iges	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	600	nA	
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 300mA		6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V _{CE} (sat)		Tj=25°C	-	2.15	2.60	V	
		, ,	V _{GE} = 15V I _C = 300A	Tj=125°C	-	2.45	-		
		(terminal)		Tj=150°C	-	2.50	-		
		V		Tj=25°C	-	1.75	2.20		
		V _{CE} (sat)		Tj=125°C	-	2.05	-		
		(chip)		Tj=150°C	-	2.10	-		
er	Internal gate resistance	Rg(int)	-		-	2.50	-	Ω	
	Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	27	-	nF	
e	Turn-on time	ton	V _{cc} = 600V	cc = 600V - 550		550	-		
- 1		tr	Ic = 300A		-	180	-		
		tr (i)	$J_{GE} = \pm 15V$ - 120			120	-	nsec	
	Turn-off time	toff	$R_G = 0.93\Omega$		-	1050	-		
		tf	Ls = 80nH	s = 80nH -		110	-		
	Forward on voltage	.,		Tj=25°C	-	2.10	2.55	V	
		V _F		Tj=125°C	-	2.25	-		
		(terminal)	$V_{GE} = 0V$	Tj=150°C	-	2.20	-		
		VF	I _F = 300A	Tj=25°C	-	1.70	2.15		
				Tj=125°C	-	1.85	-		
		(chip)		Tj=150°C	-	1.80	-	1	
	Reverse recovery time	trr	I _F = 300A		-	200	-	nsec	
5	Desistance	Ь	T=25°C T=100°C		-	5000	-	Ω	
	Resistance	R			465	495	520		
홑	B value B		T=25/50°C		3305	3375	3450	K	

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● Thermal resistance characteristics

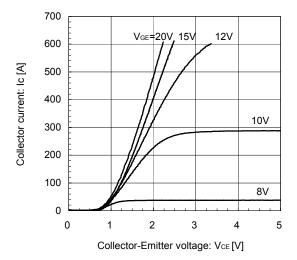
Items	Symbols	Conditions	Characteristics			Units
items	Symbols	Conditions	min.	typ.	max.	Ullits
Thermal registeres (1 device)	Rth(j-c)	Inverter IGBT	-	-	0.094	°C/W
Thermal resistance (1device)		Inverter FWD	-	-	0.150	
Contact thermal resistance (1device) (*6)	Rth(c-f)	with Thermal Compound	-	0.0167	-	

Note $^{\star}6$: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

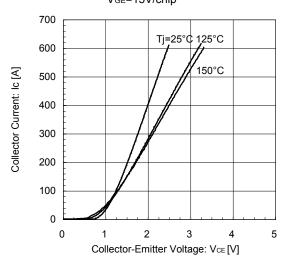
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



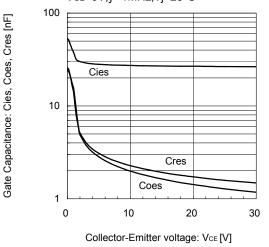
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) V_{GE}=15V/chip



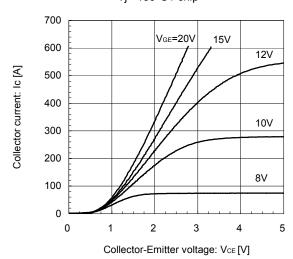
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.) $V_{GE}=0V, f=1MHz, Tj=25^{\circ}C$



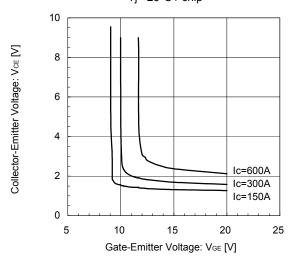
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip



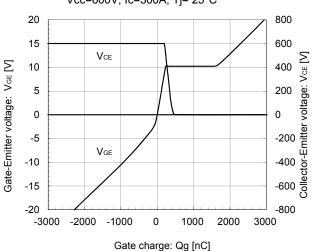
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25° C / chip

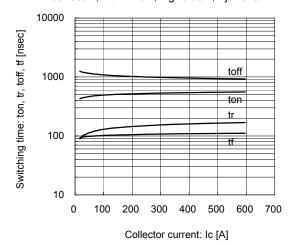


[INVERTER]

Dynamic Gate Charge (typ.) Vcc=600V, Ic=300A, Tj= 25°C

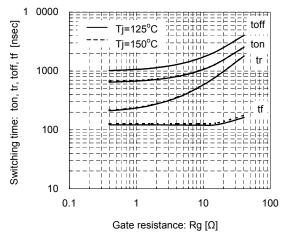


[INVERTER] Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg=0.93 Ω , Tj=25°C



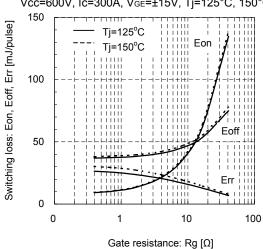
[INVERTER]

Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=300A, $V_{GE}=\pm15V$, $Tj=125^{\circ}C$, $150^{\circ}C$



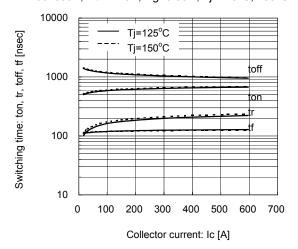
[INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=300A, V_{GE}=±15V, Tj=125°C, 150°C



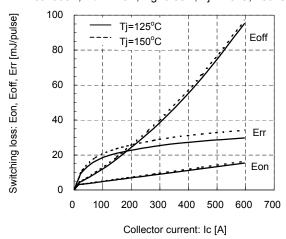
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg=0.93 Ω , Tj=125°C, 150°C



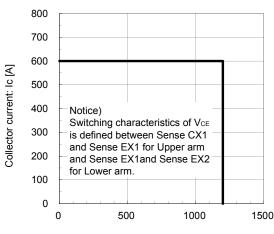
[INVERTER]

Switching loss vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg=0.93 Ω , Tj=125°C, 150°C



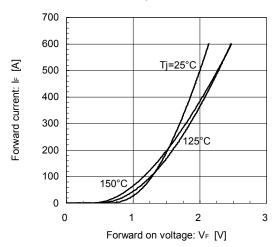
[INVERTER]

Reverse bias safe operating area (max.) +V_{GE}=15V, -V_{GE}=15V, Rg=0.93 Ω , Tj=150°C

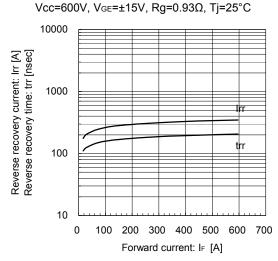


[INVERTER]

Forward Current vs. Forward Voltage (typ.) chip

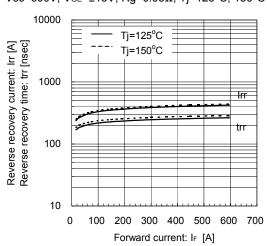


[INVERTER]
Reverse Recovery Characteristics (typ.)

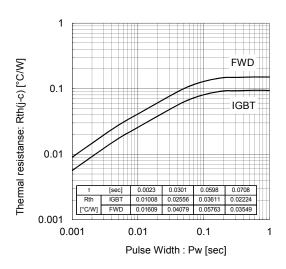


[INVERTER]

Reverse Recovery Characteristics (typ.) Vcc=600V, V_{GE}=±15V, Rg=0.93Ω, Tj=125°C, 150°C

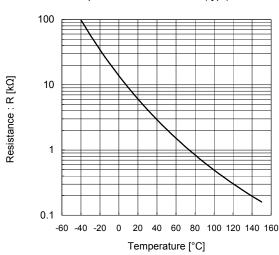


Transient Thermal Resistance (max.)

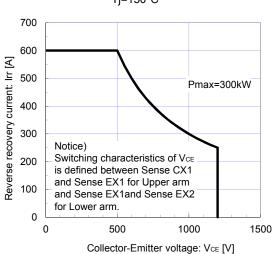


[THERMISTOR]

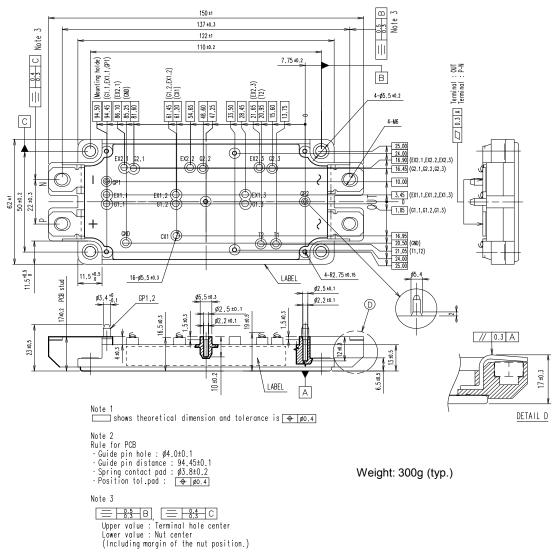
Temperature characteristic (typ.)



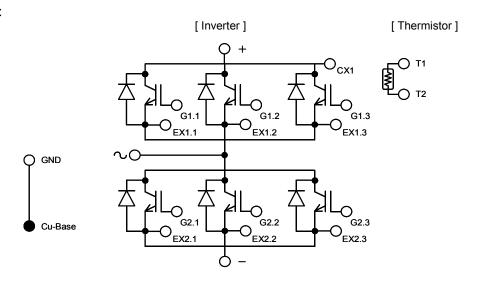
FWD safe operating area (max.)
Tj=150°C



■ Outline Drawings (Unit : mm)



■ Equivalent circuit



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- Measurement equipment

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- Safety devices

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